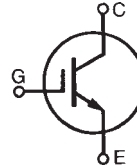


HiPerFAST™ IGBT

B2-Class High Speed IGBTs

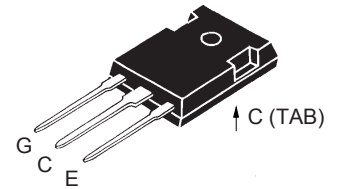
IXGH 50N90B2
IXGT 50N90B2

$$\begin{aligned} V_{CES} &= 900 \text{ V} \\ I_{C25} &= 75 \text{ A} \\ V_{CE(sat)} &= 2.7 \text{ V} \\ t_{fityp} &= 200 \text{ ns} \end{aligned}$$

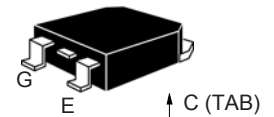


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	900	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	900	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (limited by leads)	75	A
I_{C110}	$T_C = 110^\circ\text{C}$	50	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	200	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10 \Omega$ Clamped inductive load @ $\leq 600 \text{ V}$	$I_{CM} = 100$	A
P_C	$T_C = 25^\circ\text{C}$	400	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13/10Nm/lb.in.	
Weight		TO-247 AD	6 g
		TO-268	4 g

TO-247
(IXGH)



TO-268
(IXGT)



G = Gate,
E = Emitter,

C = Collector,
TAB = Collector

Features

- High frequency IGBT
- High current handling capability
- MOS Gate turn-on
- drive simplicity

Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

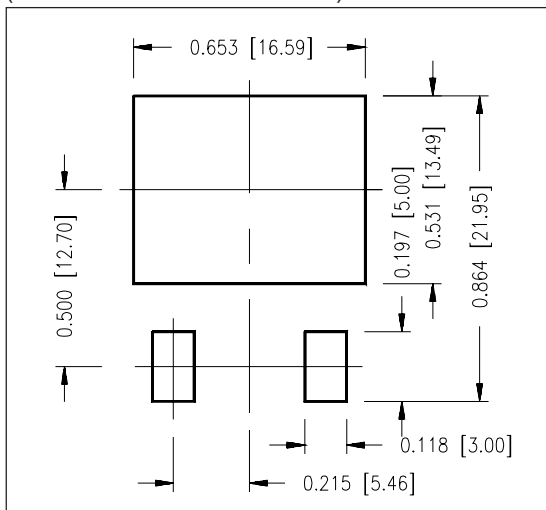
Advantages

- High power density
- Very fast switching speeds for high frequency applications

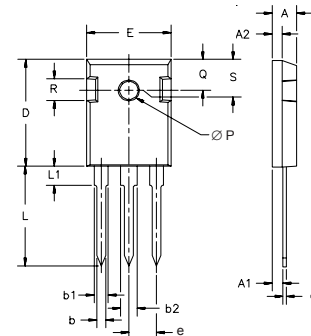
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$			50 μA 1 mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C110}$, $V_{GE} = 15 \text{ V}$		2.2	2.7 V V
	$T_J = 125^\circ\text{C}$			

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C110} A; V_{CE} = 10 V,$ Pulse test, $t \leq 300 \mu s$, duty cycle $\leq 2 \%$	25	40	S
C_{ies}	$V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz$		2500	pF
C_{oes}			180	pF
C_{res}			75	pF
Q_g	$I_C = I_{C110} A, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}$		135	nC
Q_{ge}			23	nC
Q_{gc}			50	nC
$t_{d(on)}$	Inductive load, T _J = 25°C $I_C = I_{C110} A, V_{GE} = 15 V$ $V_{CE} = 720 V, R_G = R_{off} = 5 \Omega$		20	ns
t_{ri}			28	ns
$t_{d(off)}$			350	ns
t_{fi}			200	ns
E_{off}			4.7	7.5 mJ
$t_{d(on)}$	Inductive load, T _J = 125°C $I_C = I_{C110} A, V_{GE} = 15 V$ $V_{CE} = 720 V, R_G = R_{off} = 5 \Omega$		20	ns
t_{ri}			28	ns
E_{on}			0.7	mJ
$t_{d(off)}$			400	ns
t_{fi}			420	ns
E_{off}			8.7	mJ
R_{thJC}				0.31 KW
R_{thCK}	(TO-247)		0.25	KW

Min. Recommended Footprint (Dimensions in inches and mm)

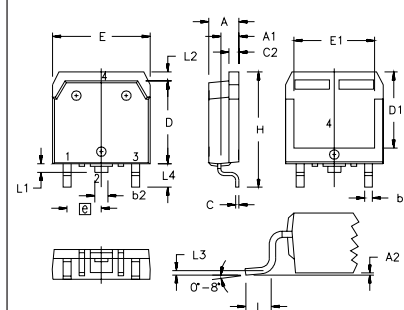


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

Fig. 1. Output Characteristics
@ 25 °C

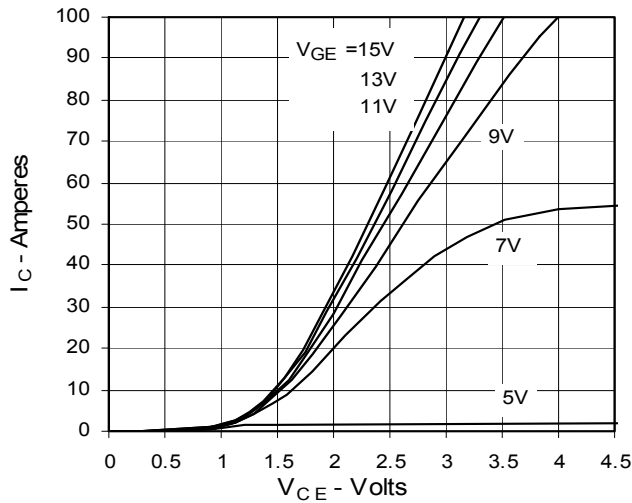


Fig. 2. Extended Output Characteristics
@ 25 °C

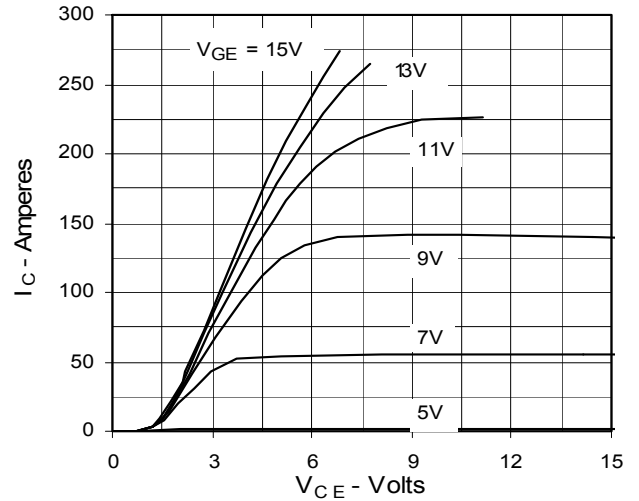


Fig. 3. Output Characteristics
@ 125 °C

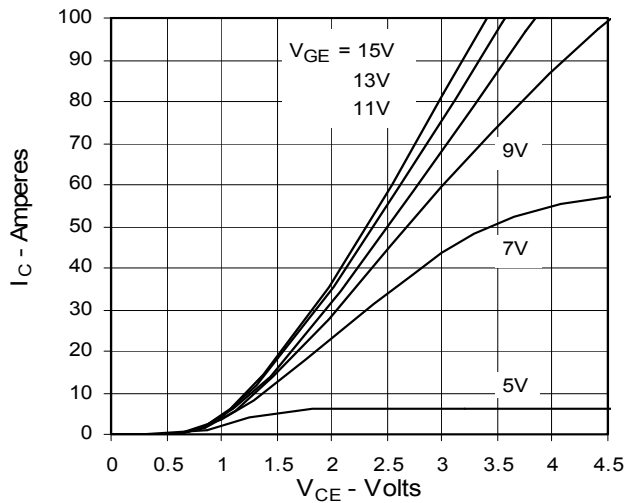


Fig. 4. Dependence of $V_{CE(sat)}$ on Temperature

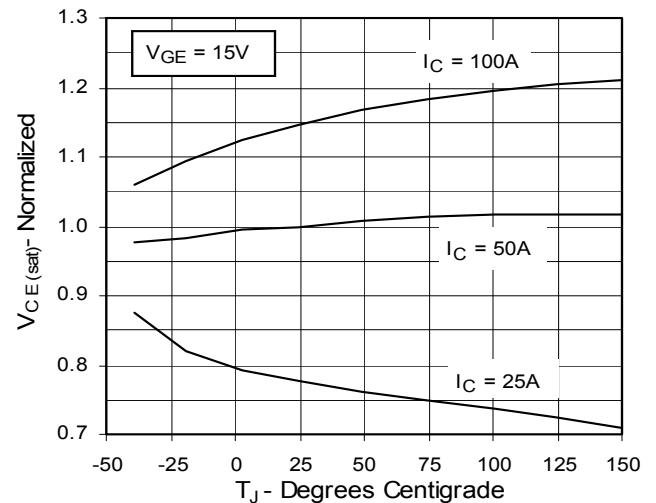


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter voltage

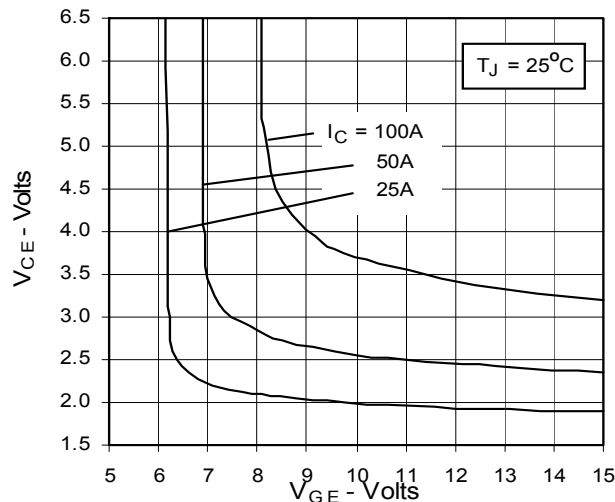


Fig. 6. Input Admittance

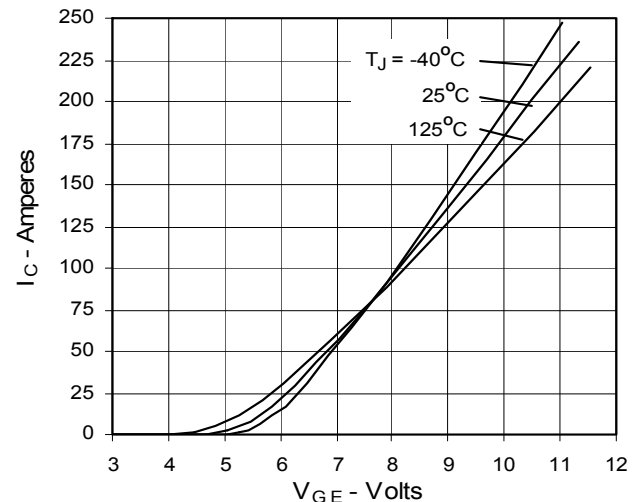
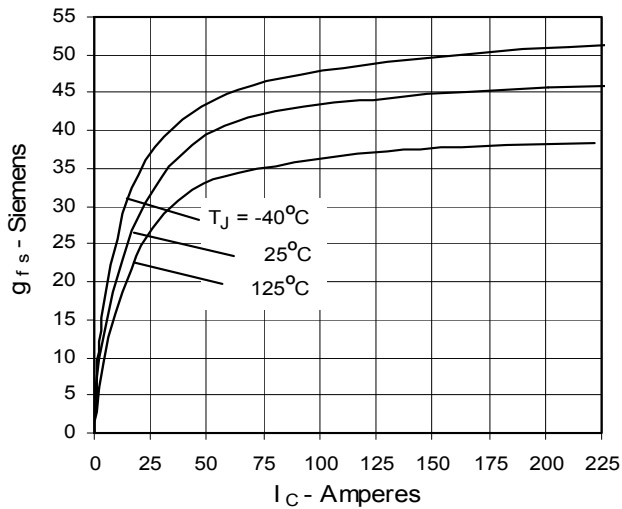
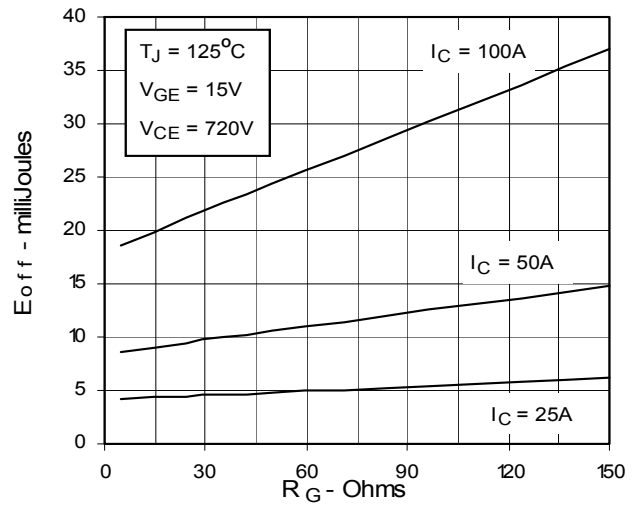
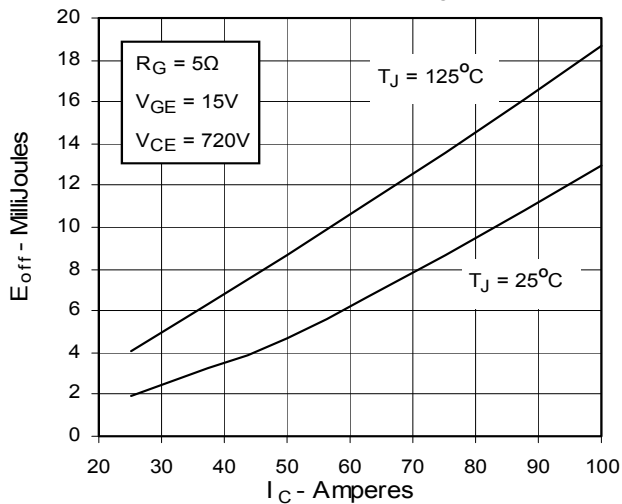
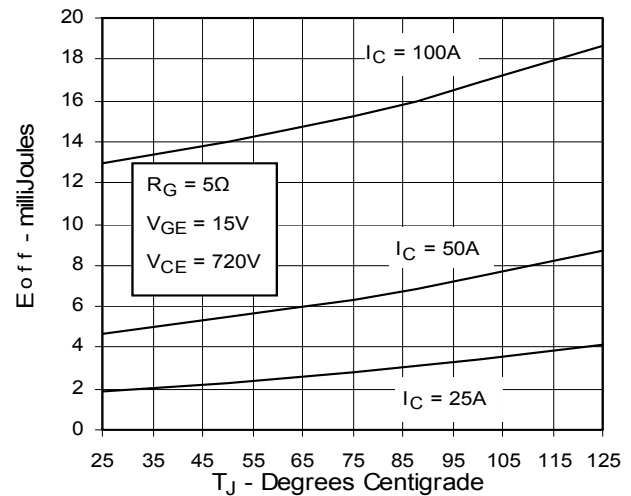
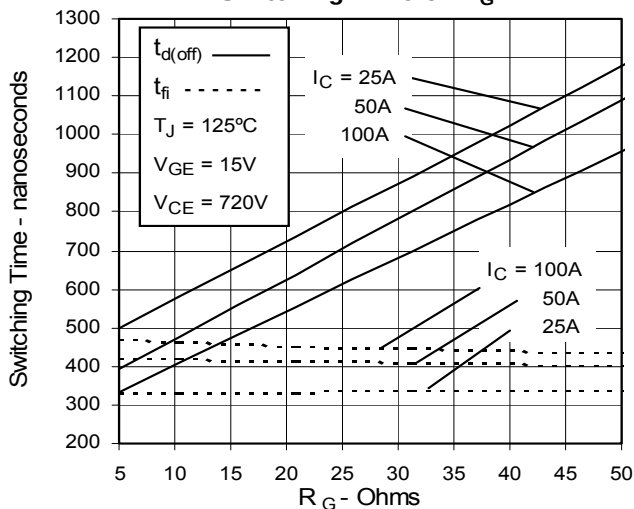
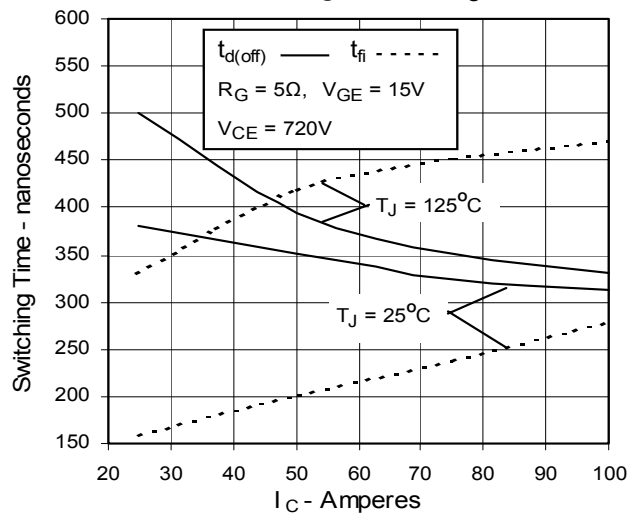


Fig. 7. Transconductance

Fig. 8. Dependence of Turn-off Energy Loss on R_G

Fig. 9. Dependence of Turn-Off Energy Loss on I_C

Fig. 10. Dependence of Turn-off Energy Loss on Temperature

Fig. 11. Dependence of Turn-off Switching Time on R_G

Fig. 12. Dependence of Turn-off Switching Time on I_C


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4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

Fig. 13. Dependence of Turn-off Switching Time on Temperature

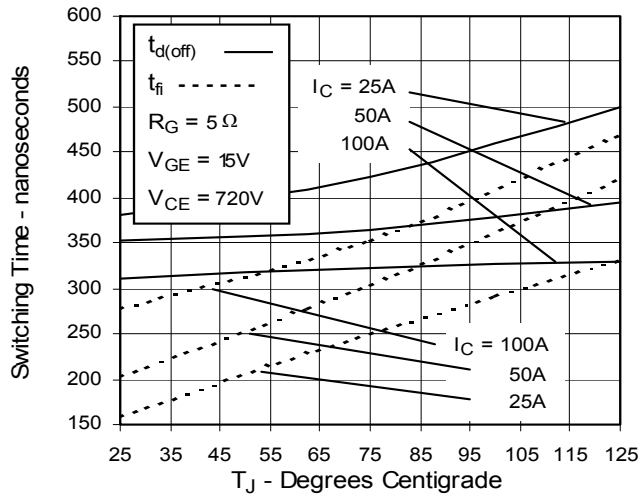


Fig. 14. Gate Charge

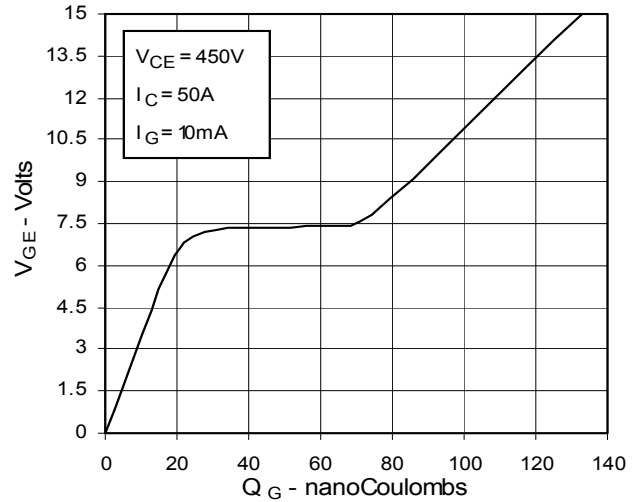


Fig. 15. Capacitance

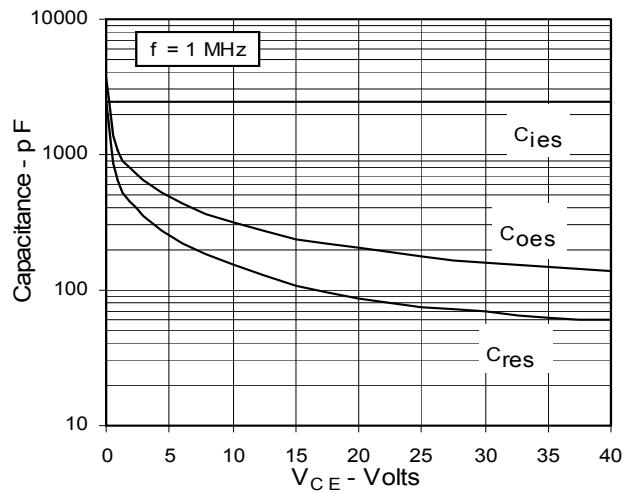


Fig. 16. Reverse-Bias Safe Operating Area

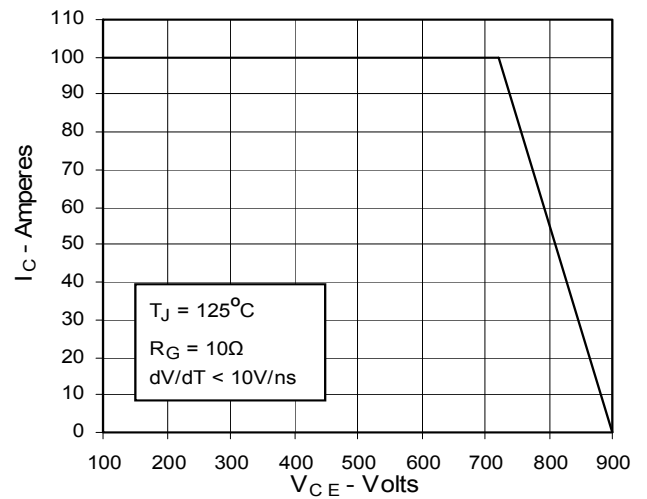


Fig. 17. Maximum Transient Thermal Resistance

